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SPECIFICATION 50mW CW CWDM DFB Chip DL-DFB31050D-75-85E



A. PRODUCT DESCRIPTION

DenseLight DL-DFB31050D-75-85E is an uncooled DFB laser diode operating with a minimum output power of 50mW at 75°C for 1311 nm wavelength and engineered for CW transmission.

B. FEATURES

- Uncooled operation from -5 to 75°C
- Minimum output power of 50mW at 75°C, 210mA (typical)
- Typical lasing wavelength of 1311 nm
- Typical SMSR \geq 35dB
- Designed for CW transmission

C. PACKAGING

• DFB laser diode (chip) with coated facets

D. APPLICATIONS

• Ethernet/Data Center

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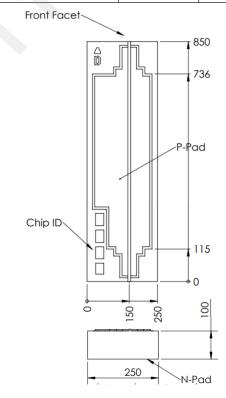
E. ABSOLUTE MAXIMUM RATINGS

Operation beyond the absolute maximum ratings can cause degradation in device performance leading to permanent damage to the device.

Parameter	Symbol	Condition	Min	Max	Unit
Reverse voltage	V_R	-	-	2	V
Forward current	I_{F}	-	-	500	mA
Operating temperature	Top	-	-5	75	°C
Storage temperature	T_{stg}	Ambient	-40	85	°C
Operating & Storage Humidity	RH	Relative humidity of surrounding environment. Non hermetic package.	8	85	%
Electro static discharge (ESD)	V_{ESD}	HBM	-	500	V

F. PHYSICAL CHARACTERISTICS

Parameter	Symbol	Typical	Unit
Chip dimensions	$L \times W \times H$	(850±20) × (250±20) × (100±10)	μm
Distance of optical axis from p-top contact	-	7.6±0.75	μm
Horizontal distance of optical axis from left edge of the chip (with front facet facing upwards)	-	150±15	μm



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G. OPTICAL, ELECTRICAL AND THERMAL CHARACTERISTICS

Performance is based on laser diode die singulated from bar and mounted onto heat-dissipating submount.

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Operating temperature	T _{op}	-	-5	-	75	°C
Threshold current	I_{th}	$T_{op} = 25^{\circ}C$	-	30) -	mA
		Over full Top range	-	60	-	mA
Operating current	I_{op}	CW, $P_o = 50 \text{mW}$, $T_{op} = 75^{\circ}\text{C}$ at λ_c	2	210	230	mA
Forward voltage	$V_{\rm f}$	Over full Top and Iop range		-	1.35	V
Slope efficiency	η_{s}	Over full Top and Iop range	0.2	-	-	W/A
Optical Output Power	Po	$I_{op} \ll I_{op, max},$ over full T_{op} range	50	-	-	mW
Center wavelength	λ_{c}	CW, at over operating temperature range	1304.5	1311	1317.5	nm
Side Mode Suppression Ratio	SMSR	Over full Top and Iop range	35	-	-	dB
Wavelength change with temperature	$\Delta \lambda / \Delta T$	Over full Top range	0.09	0.1	0.11	nm/°C
Far Field Divergence Angle Horizontal	$\theta_{ m H}$	CW, FWHM	-	17	30	degree
Far Field Divergence Angle Vertical	$\theta_{ m V}$	CW, FWHM	-	24	30	degree

Note:

- 1. Laser I-V curve must be monotonic and free of kinks.
- 2. T_{op} is measured by a thermistor soldered on the submount where the laser diode chip is soldered on to.

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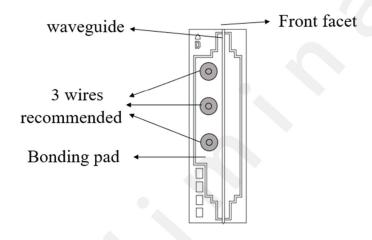
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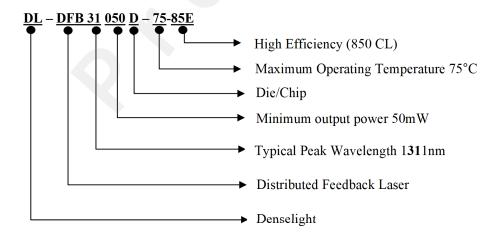
H. ASSEMBLY

Recommended Wire Bonding Instructions:

- 1. Gold wire diameter = $25.4\mu m$.
- 2. Ball bonding should be used and wedge bonding is to be avoided.
- 3. Recommended number of wires = 3 or more for better heat dissipation and current spreading.
- 4. Wire bonds should be distributed uniformly on the p-bond pad but positioned away from the waveguide.



I. ORDER INFORMATION



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